

## AMENDMENTS TO THE CLAIMS

**This listing of claims will replace all prior versions and listings of claims in the application:**

### LISTING OF CLAIMS:

1. (Currently Amended) A method of producing a glass substrate for ~~[[a]]~~ an EUV (extreme ultra violet) mask blank, the method comprising:

a preparing step of preparing the glass substrate having a surface subjected to precision polishing;

a profile measuring step of measuring, after the preparing step, a convex/concave profile of ~~[[a]]~~ the surface of the glass substrate ~~for a mask blank~~;

a flatness control step of controlling a flatness of the surface of the glass substrate to a value not greater than a reference value determined depending upon a required flatness required to the glass substrate by specifying the degree of convexity of a convex portion present on the surface of the glass substrate with reference to a result of measurement obtained in the profile measuring step and executing local machining upon the convex portion under a machining condition depending upon the degree of convexity, the local machining being carried out by plasma etching or a gas cluster ion beam; ~~and~~

an acid treatment step of subjecting, after the flatness control step, the surface of the glass substrate to acid treatment under a condition that machining scraps of the glass substrate, a reaction product, and a machining-affected layer produced by the local machining and left on the surface of the glass substrate are removed while maintaining the flatness and a surface roughness of the glass substrate; and

a polishing step of polishing, ~~after the flatness control step~~ acid treatment step, the surface of the glass substrate ~~subjected to the local machining~~; wherein:

~~the surface of the glass substrate subjected to the local machining is subjected to acid treatment in an acid treatment step after the flatness control step and before the polishing step, said acid treatment step thereby removing machining scraps of the glass substrate, a reaction product, and a machining-affected layer produced by the local machining by the plasma etching or the gas cluster ion beam and left on the surface of the glass substrate;~~

said method producing, as said glass substrate, ~~a glass substrate for an EUV (extreme ultra violet) mask blank and comprising said flatness control step, said acid treatment step, and~~

~~said polishing step carried out in this order to~~ thereby ~~make~~ making the surface of the glass substrate have a flatness and a surface roughness required ~~to of~~ the glass substrate for producing the EUV mask blank.

2. (Currently Amended) A method of producing a glass substrate for ~~[[a]]~~ an EUV (extreme ultra violet) mask blank, the method comprising:

a preparing step of preparing the glass substrate having a surface subjected to precision polishing;

a profile measuring step of measuring, after the preparing step, a convex/concave profile of ~~[[a]]~~ the surface of the glass substrate ~~for a mask blank;~~

a flatness control step of controlling a flatness of the surface of the glass substrate to a value not greater than a reference value determined depending upon a required flatness required to the glass substrate by specifying the degree of convexity of a convex portion present on the surface of the glass substrate with reference to a result of measurement obtained in the profile measuring step and executing local machining upon the convex portion under a machining condition depending upon the degree of convexity, the local machining being carried out by plasma etching or a gas cluster ion beam; ~~and~~

an alkali treatment step of subjecting, after the flatness control step, the surface of the glass substrate to alkali treatment under a condition that machining scraps of the glass substrate, a reaction product, and a machining-affected layer produced by the local machining and left on the surface of the glass substrate are removed while maintaining the flatness and a surface roughness of the glass substrate; and

a polishing step of polishing, ~~after the flatness control step~~ alkali treatment step, the surface of the glass substrate ~~subjected to the local machining; wherein:~~

~~the surface of the glass substrate subjected to the local machining is subjected to alkali treatment in an alkali treatment step after the flatness control step and before the polishing step, said alkali treatment step thereby removing machining scraps of the glass substrate, a reaction product, and a machining-affected layer produced by the local machining by the plasma etching or the gas cluster ion beam and left on the surface of the glass substrate;~~

~~said method producing, as said glass substrate, a glass substrate for an EUV (extreme ultra violet) mask blank and comprising said flatness control step, said alkali treatment step, and said polishing step carried out in this order to~~ thereby ~~make~~ making the surface of the glass

substrate have a flatness and a surface roughness required ~~to~~ of the glass substrate for producing the EUV mask blank.

**3. (canceled).**

4. (Previously Presented) A method according to claim 1, wherein an acid used in the acid treatment is fluorosilic acid and/or hydrofluoric acid.

5. (Original) A method according to claim 1, wherein an acid used in the acid treatment is sulfuric acid.

6. (Original) A method according to claim 1, wherein the surface of the glass substrate subjected to the acid treatment is subjected to alkali treatment after the acid treatment.

7. (Currently Amended) A method according to claim 1, wherein the reference value is not greater than ~~0.5~~ 0.05  $\mu\text{m}$ .

8. (Currently Amended) A method of producing a mask blank, the method comprising the steps of preparing the glass substrate obtained by the method according to ~~any one of claims 1 to 7~~ claim 1, and forming a thin film as a transferred pattern on the glass substrate.

9. (Original) A method of producing a transfer mask, the method comprising the steps of preparing the mask blank obtained by the method according to claim 8 and patterning the thin film of the mask blank to form a thin film pattern on the glass substrate.

10. (Original) A method of producing a semiconductor device, the method comprising the steps of preparing the transfer mask obtained by the method according to claim 9 and transferring the thin film pattern of the transfer mask onto a semiconductor substrate by lithography.

**11. (Canceled).**

12. (Currently Amended) A method according to claim 2, wherein the reference value is not greater than ~~0.5~~ 0.05  $\mu\text{m}$ .

13. (Currently Amended) A method of producing a mask blank, the method comprising the steps of preparing the glass substrate obtained by the method according to ~~any one of claims 11 and 12~~ claim 2, and forming a thin film as a transferred pattern on the glass substrate.

14. (Previously Presented) A method of producing a transfer mask, the method comprising the steps of preparing the mask blank obtained by the method according to claim 13 and patterning the thin film of the mask blank to form a thin film pattern on the glass substrate.

15. (Previously Presented) A method of producing a semiconductor device, the method comprising the steps of preparing the transfer mask obtained by the method according to claim 14 and transferring the thin film pattern of the transfer mask onto a semiconductor substrate by lithography.

16. (Previously Presented) A method according to claim 1, wherein said flatness control step, said alkali treatment step, and said polishing step are carried out in this order to thereby make the surface of the glass substrate have a surface roughness Ra of 0.2 nm or less, where the surface roughness Ra is representative of a center-line-mean roughness.

17. (Previously Presented) A method according to claim 2, wherein said flatness control step, said alkali treatment step, and said polishing step are carried out in this order to thereby make the surface of the glass substrate have a surface roughness Ra of 0.2 nm or less, where the surface roughness Ra is representative of a center-line-mean roughness.

18. (Previously Presented) A method according to claim 1, wherein said glass substrate makes use of a SiO<sub>2</sub>-TiO<sub>2</sub> glass.

19. (Previously Presented) A method according to claim 18, wherein concentration of acid used in the acid treatment is 0.05-10 vol%.

20. (Previously Presented) A method according to claim 2, wherein said glass substrate makes use of a SiO<sub>2</sub>-TiO<sub>2</sub> glass.

21. (Previously Presented) A method according to claim 20, wherein concentration of alkali used in the alkali treatment is 0.5-10 vol%.

**22. - 24. (Canceled).**